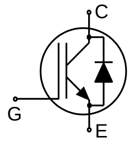
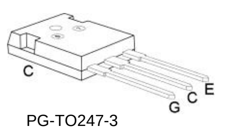
Low Loss DuoPack : IGBT in TRENCHSTOP™ and Fieldstop technology with soft, fast recovery anti-parallel Emitter Controlled HE diode

RoHS Green





Features:

- Very low $V_{CE(sat)}$ 1.5V (typ.)
- Maximum Junction Temperature 175°C
- Short circuit withstand time 5µs
- Designed for :
  - Frequency Converters
  - Uninterrupted Power Supply
- TRENCHSTOP™ and Fieldstop technology for 600V applications offers :
  - very tight parameter distribution
  - high ruggedness, temperature stable behavior
  - very high switching speed
  - low $V_{CE(sat)}$
- Positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Very soft, fast recovery anti-parallel Emitter Controlled HE diode
- Qualified according to JEDEC[1] for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : http://www.infineon.com/igbt/

Type	V_{CE}	I_C	$V_{CE(sat),Tj=25°C}$	$T_{j,max}$	Marking	Package
IKW20N60T	600V	20A	1.5V	175°C	K20T60	PG-TO247-3

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_j \geq 25°C$	V_{CE}	600	V
DC collector current, limited by T_{jmax} $T_C = 25°C$	I_C	41	A
$T_C = 100°C$		28	
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	60	
Turn off safe operating area, $V_{CE} = 600V$, $T_j = 175°C$, $t_p = 1µs$	-	60	
Diode forward current, limited by T_{jmax} $T_C = 25°C$	I_F	41	
$T_C = 100°C$		28	
Diode pulsed current, t_p limited by T_{jmax}	I_{Fpuls}	60	
Gate-emitter voltage	V_{GE}	±20	V
Short circuit withstand time[2)] $V_{GE} = 15V$, $V_{CC} \leq 400V$, $T_j \leq 150°C$	t_{SC}	5	µs
Power dissipation $T_C = 25°C$	P_{tot}	166	W
Operating junction temperature	T_j	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

[1] J-STD-020 and JESD-022

[2)] Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		0.9	K/W
Diode thermal resistance, junction – case	R_{thJCD}		1.5	
Thermal resistance, junction – ambient	R_{thJA}		40	

Electrical Characteristic, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE}=0V, I_C=0.2mA	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	V_{GE} = 15V, I_C=20A T_j=25°C T_j=175°C	- -	1.5 1.9	2.05 -	
Diode forward voltage	V_F	V_{GE}=0V, I_F=20A T_j=25°C T_j=175°C	- -	1.65 1.6	2.05 -	
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C=290µA, V_{CE}=V_{GE}	4.1	4.9	5.7	
Zero gate voltage collector current	I_{CES}	V_{CE}=600V, V_{GE}=0V T_j=25°C T_j=175°C	- -	- -	40 1500	µA
Gate-emitter leakage current	I_{GES}	V_{CE}=0V, V_{GE}=20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE}=20V, I_C=20A	-	11	-	S
Integrated gate resistor	R_{Gint}			-		Ω

Dynamic Characteristic

Parameter	Symbol	Conditions	min.	Typ.	max.	Unit
Input capacitance	C_{iss}	V_{CE}=25V,	-	1100	-	pF
Output capacitance	C_{oss}	V_{GE}=0V,	-	71	-	
Reverse transfer capacitance	C_{rss}	f=1MHz	-	32	-	
Gate charge	Q_{Gate}	V_{CC}=480V, I_C=20A V_{GE}=15V	-	120	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E	PG-TO247-3	-	13	-	nH
Short circuit collector current[1)]	$I_{C(SC)}$	V_{GE}=15V, t_{SC}≤5µs V_{CC} = 400V, T_j ≤ 150°C	-	183.3	-	A

[1)] Allowed number of short circuits: <1000; time between short circuits: >1s.

Switching Characteristic, Inductive Load, at T_j=25 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=25°C, V_{CC}=400V, I_C=20A, V_{GE}=0/15V, r_G=12Ω, L_σ=131nH, C_σ=31pF L_σ, C_σ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	18	-	ns
Rise time	t_r		-	14	-	
Turn-off delay time	$t_{d(off)}$		-	199	-	
Fall time	t_f		-	42	-	
Turn-on energy	E_{on}		-	0.31	-	mJ
Turn-off energy	E_{off}		-	0.46	-	
Total switching energy	E_{ts}		-	0.77	-	
Anti-Parallel Diode Characteristic						
Diode reverse recovery time	t_{rr}	T_j=25°C, V_R=400V, I_F=20A, di_F/dt=880A/µs	-	41	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.31	-	µC
Diode peak reverse recovery current	I_{rrm}		-	13.3	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	711	-	A/µs

Switching Characteristic, Inductive Load, at T_j=175 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=175°C, V_{CC}=400V, I_C=20A, V_{GE}=0/15V, r_G=12Ω, L_σ=131nH, C_σ=31pF L_σ, C_σ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	18	-	ns
Rise time	t_r		-	18	-	
Turn-off delay time	$t_{d(off)}$		-	223	-	
Fall time	t_f		-	76	-	
Turn-on energy	E_{on}		-	0.51	-	mJ
Turn-off energy	E_{off}		-	0.64	-	
Total switching energy	E_{ts}		-	1.15	-	
Anti-Parallel Diode Characteristic						
Diode reverse recovery time	t_{rr}	T_j=175°C V_R=400V, I_F=20A, di_F/dt=880A/µs	-	176	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.46	-	µC
Diode peak reverse recovery current	I_{rrm}		-	18.9	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	467	-	A/µs

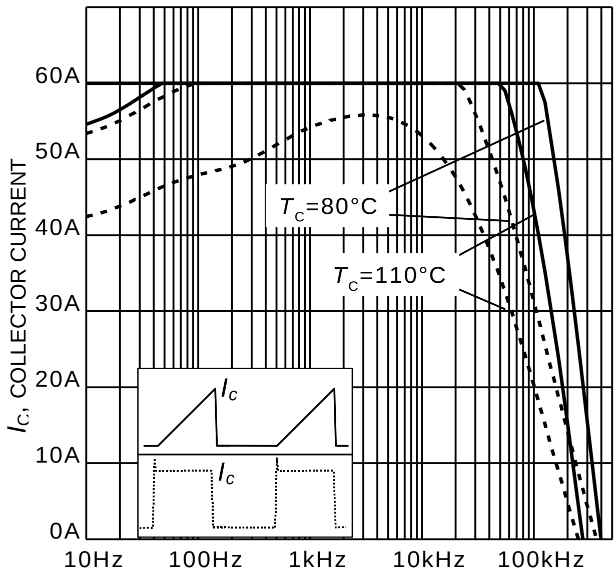


Figure 1. Collector current as a function of switching frequency
($T_j \leq 175°C$, $D = 0.5$, $V_{CE} = 400V$, $V_{GE} = 0/15V$, $r_G = 12\Omega$)

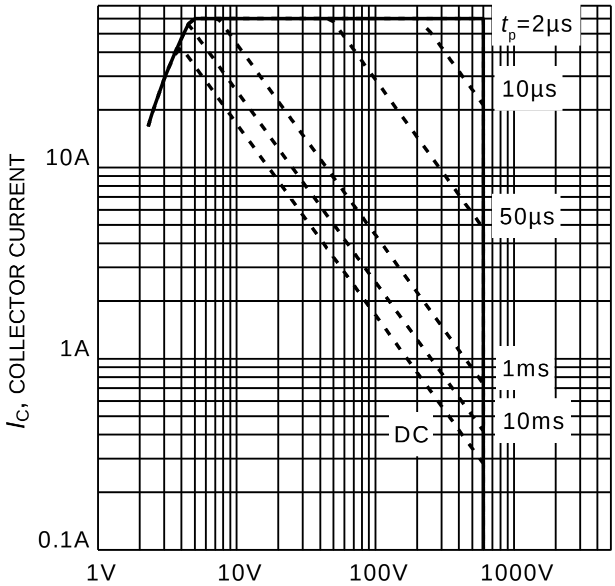


Figure 2. Safe operating area
($D = 0$, $T_C = 25°C$, $T_j \leq 175°C$; V_{GE}=0/15V)

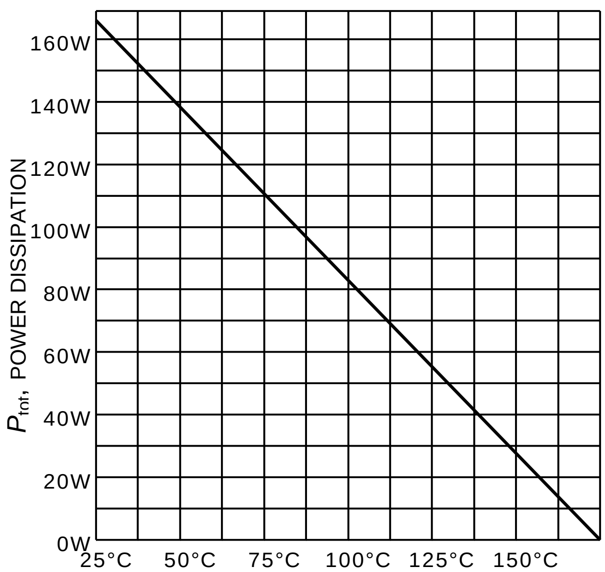


Figure 3. Power dissipation as a function of case temperature
($T_j \leq 175°C$)

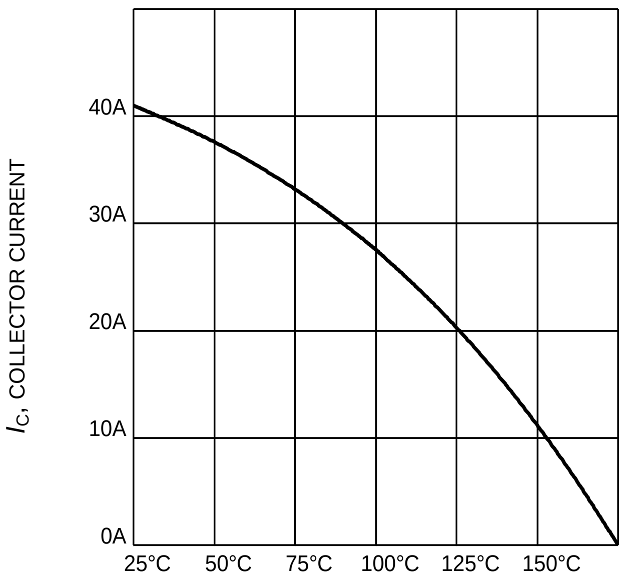


Figure 4. Collector current as a function of case temperature
($V_{GE} \geq 15V$, $T_j \leq 175°C$)

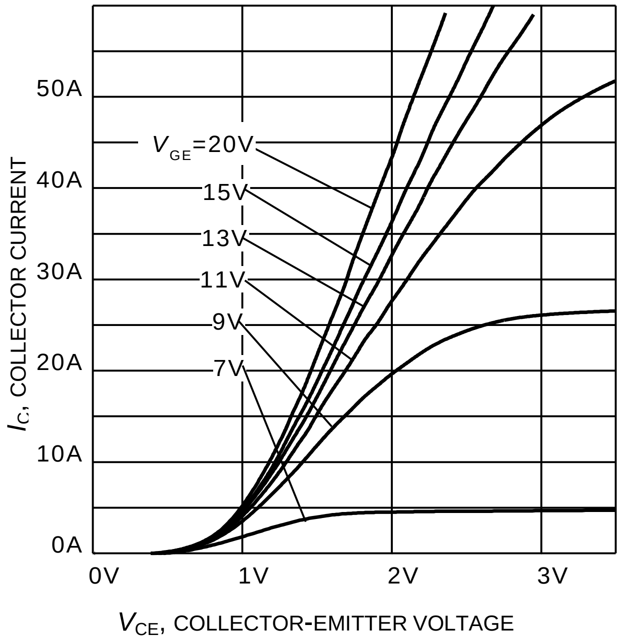


Figure 5. Typical output characteristic
(T_j = 25°C)

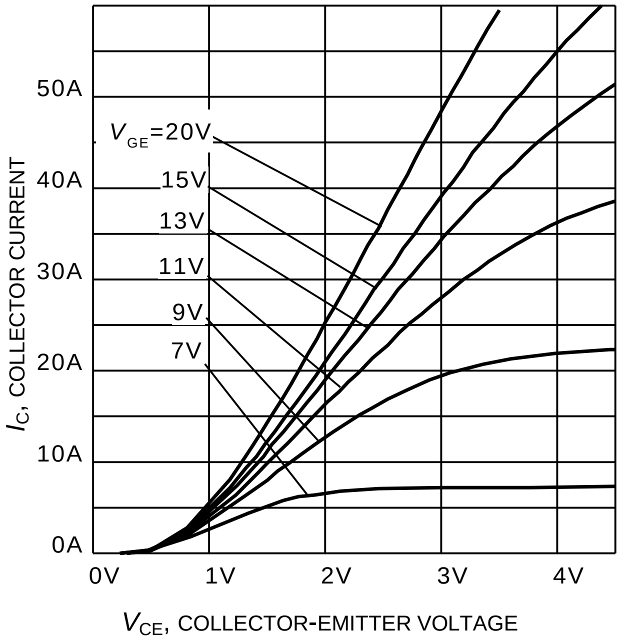


Figure 6. Typical output characteristic
(T_j = 175°C)

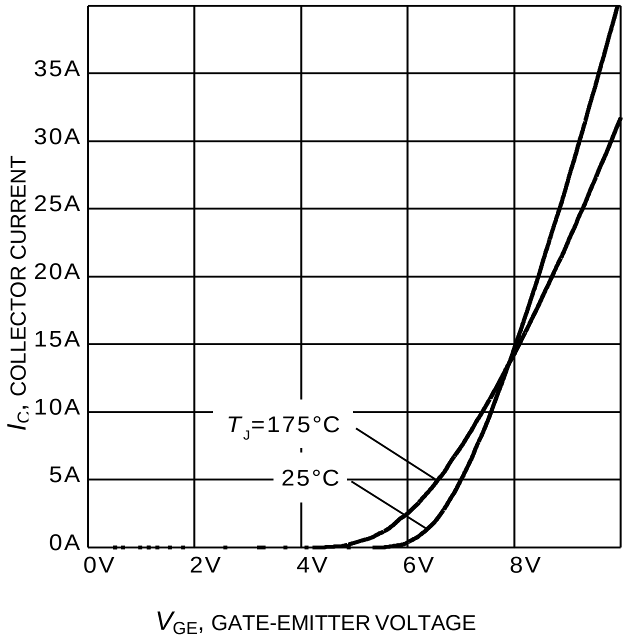


Figure 7. Typical transfer characteristic
(V_{CE}=10V)

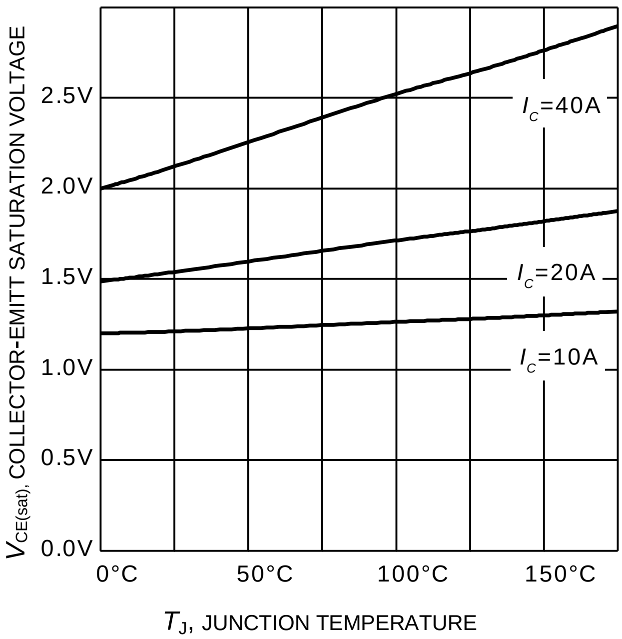


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
(V_{GE} = 15V)

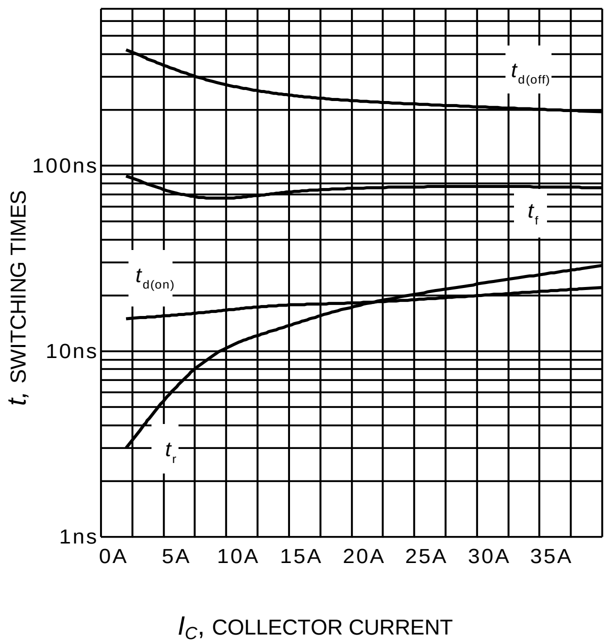


Figure 9. Typical switching times as a function of collector current
(inductive load, T_J=175°C, V_{CE} = 400V, V_{GE} = 0/15V, r_G = 12Ω, Dynamic test circuit in Figure E)

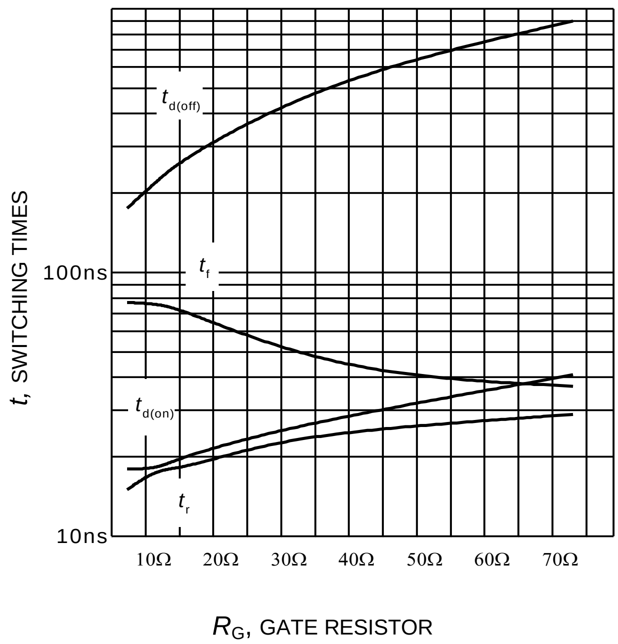


Figure 10. Typical switching times as a function of gate resistor
(inductive load, T_J = 175°C, V_{CE}= 400V, V_{GE} = 0/15V, I_C = 20A, Dynamic test circuit in Figure E)

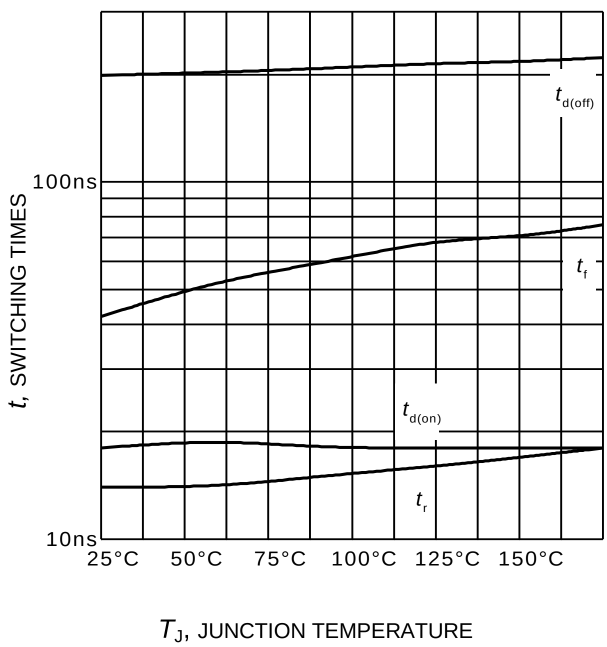


Figure 11. Typical switching times as a function of junction temperature
(inductive load, V_{CE} = 400V, V_{GE} = 0/15V, I_C = 20A, r_G=12Ω, Dynamic test circuit in Figure E)

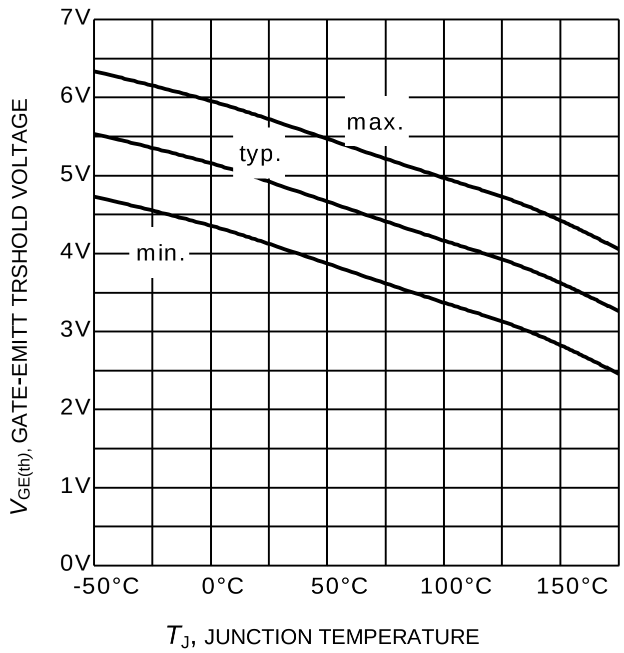


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
(I_C = 0.29mA)

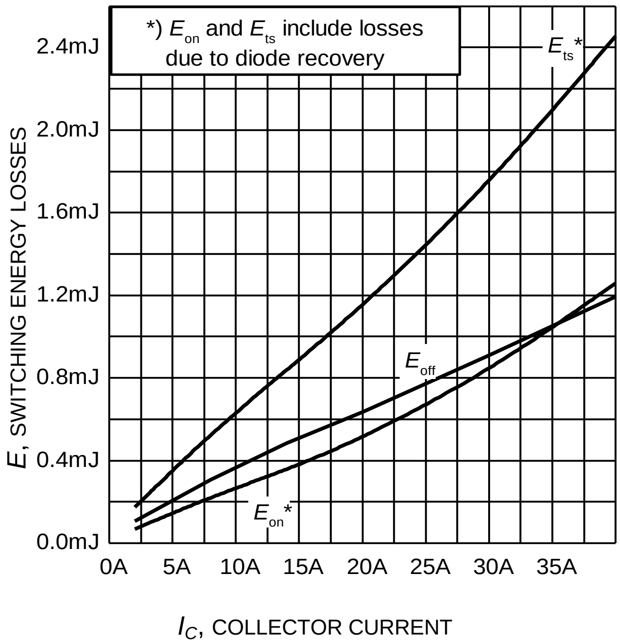


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, T_J = 175°C, V_{CE} = 400V, V_{GE} = 0/15V, r_G = 12Ω, Dynamic test circuit in Figure E)

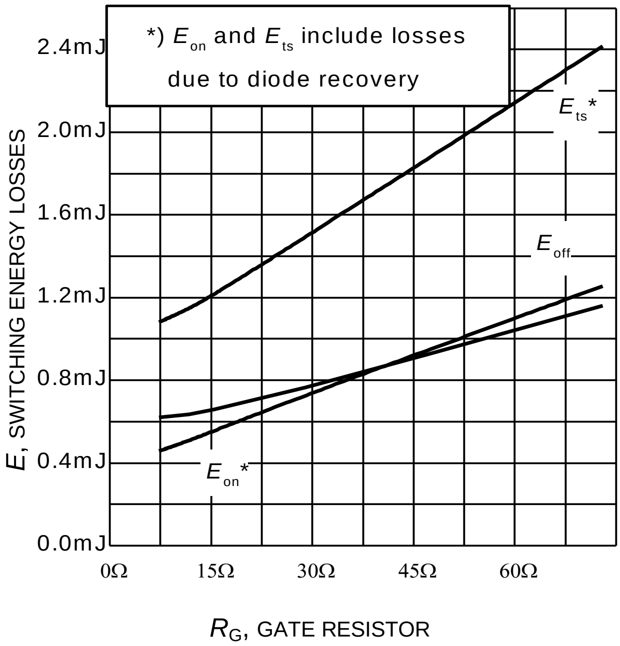


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, T_J = 175°C, V_{CE} = 400V, V_{GE} = 0/15V, I_C = 20A, Dynamic test circuit in Figure E)

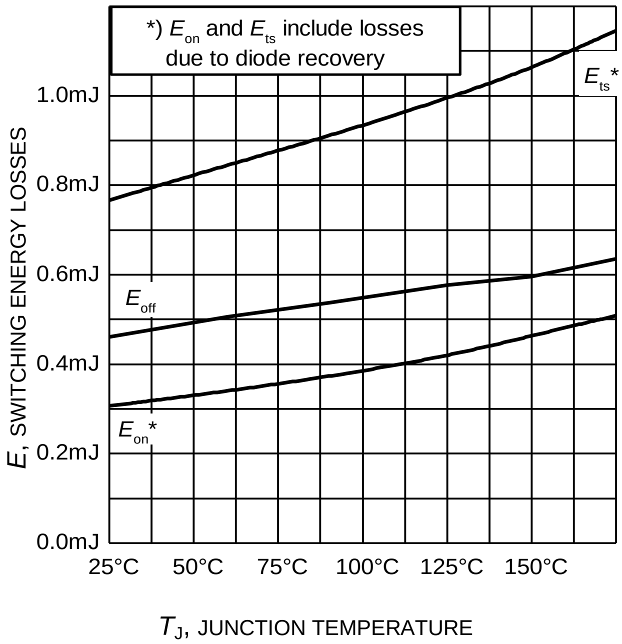


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, V_{CE} = 400V, V_{GE} = 0/15V, I_C = 20A, r_G = 12Ω, Dynamic test circuit in Figure E)

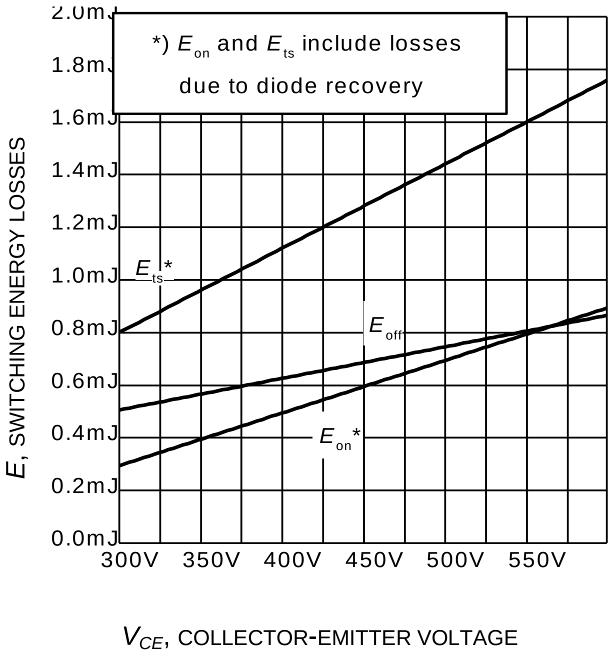


Figure 16. Typical switching energy losses as a function of collector emitter voltage
(inductive load, T_J = 175°C, V_{GE} = 0/15V, I_C = 20A, r_G = 12Ω, Dynamic test circuit in Figure E)

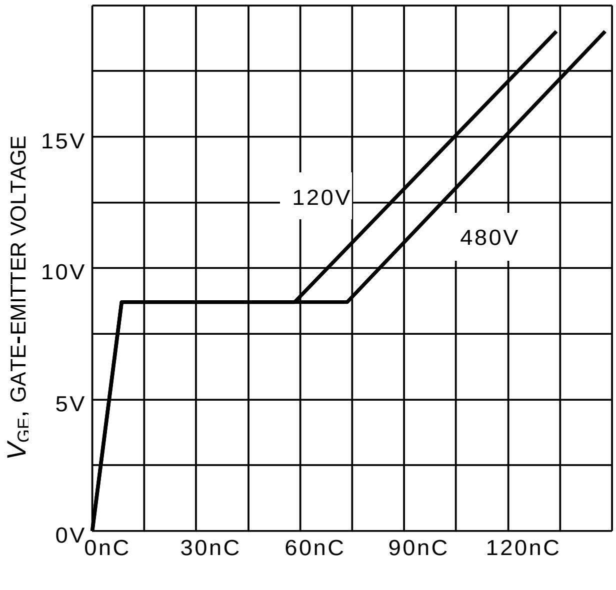


Figure 17. Typical gate charge
(I_C=20 A)

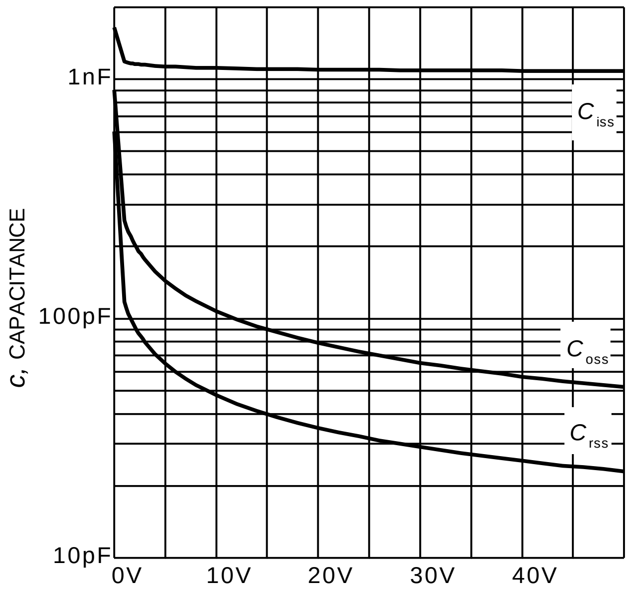


Figure 18. Typical capacitance as a function of collector-emitter voltage
(V_{GE}=0V, f = 1 MHz)

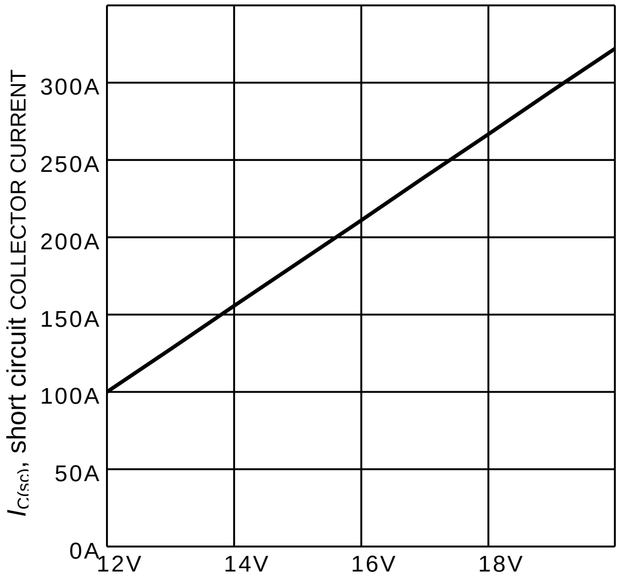


Figure 19. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \leq$ 400V, $T_j \leq$ 150°C)

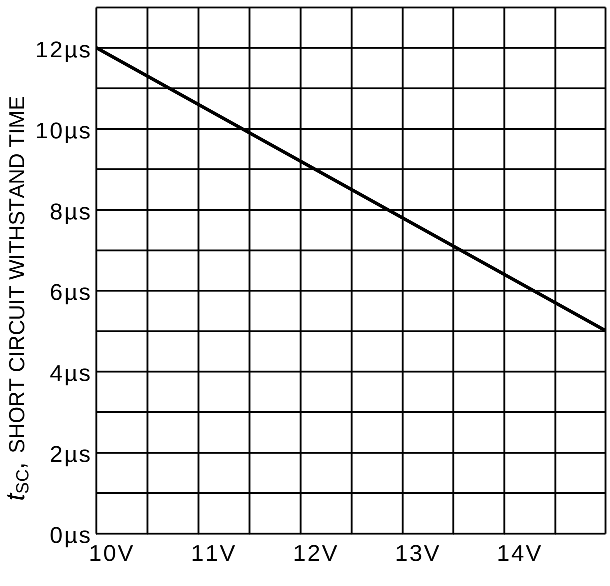


Figure 20. Short circuit withstand time as a function of gate-emitter voltage
(V_{CE}=400V, start at T_J=25°C, T_{Jmax}<150°C)

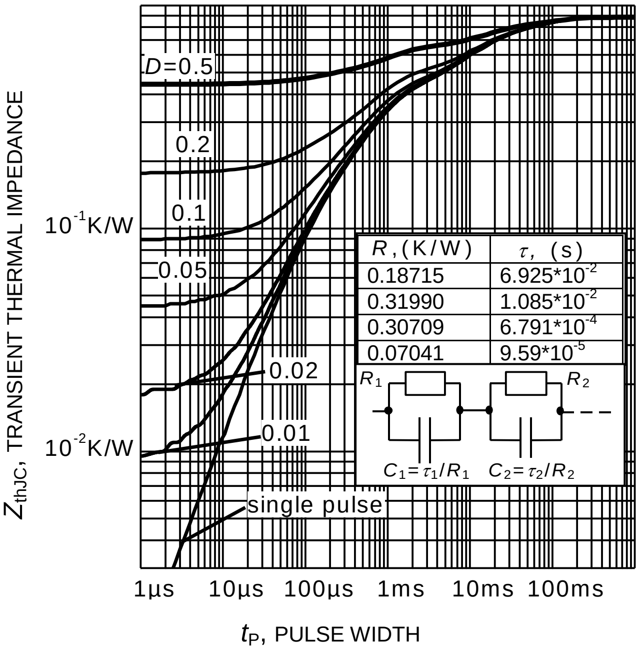


Figure 21. IGBT transient thermal impedance
($D = t_p$ / T)

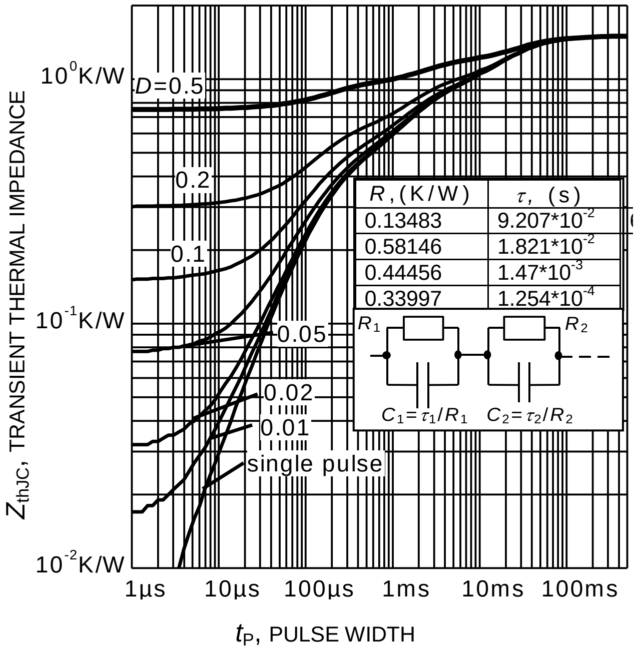


Figure 22. Diode transient thermal impedance as a function of pulse width
($D=t_P/T$)

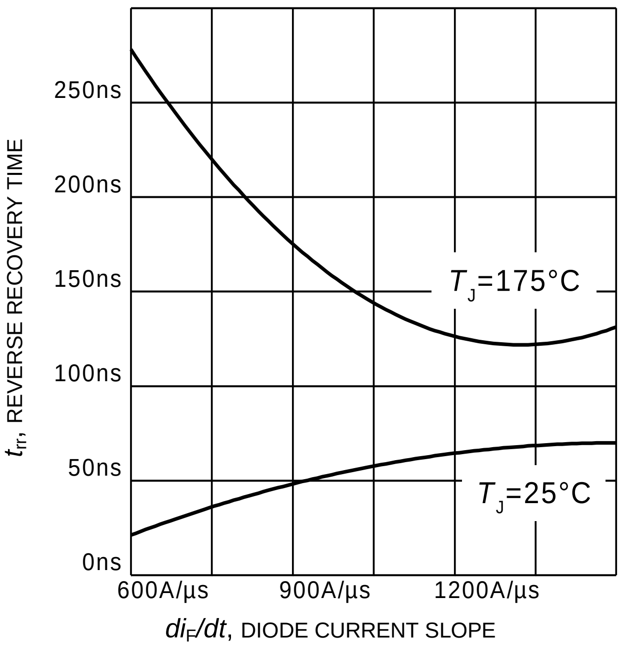


Figure 23. Typical reverse recovery time as a function of diode current slope
(V_R=400V, I_F=20A,
Dynamic test circuit in Figure E)

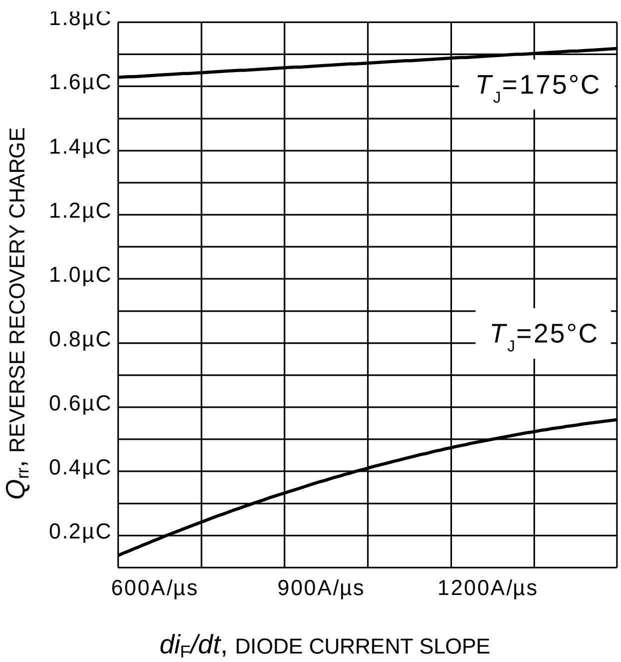


Figure 24. Typical reverse recovery charge as a function of diode current slope
(V_R = 400V, I_F = 20A,
Dynamic test circuit in Figure E)

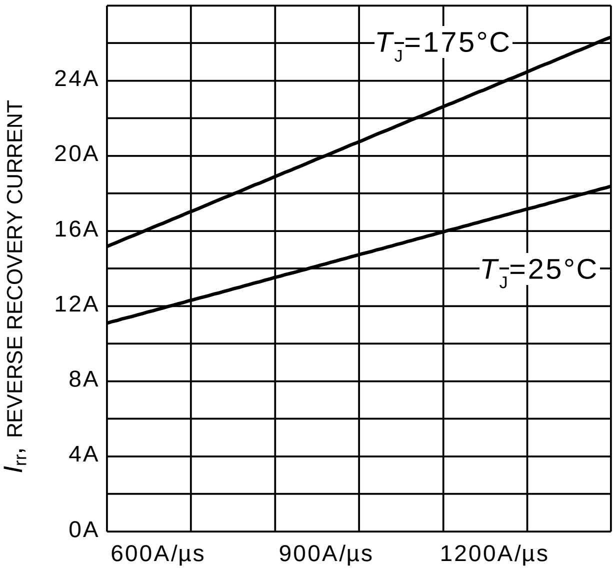


Figure 25. Typical reverse recovery current as a function of diode current slope
(V_R = 400V, I_F = 20A,
Dynamic test circuit in Figure E)

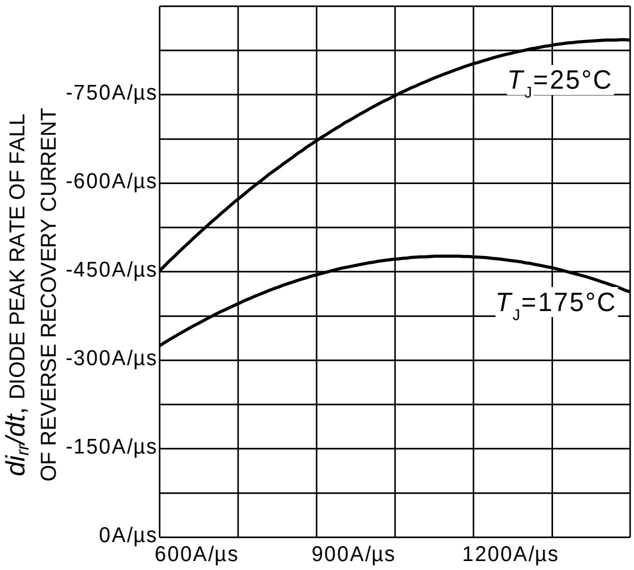


Figure 26. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope
(V_R=400V, I_F=20A,
Dynamic test circuit in Figure E)

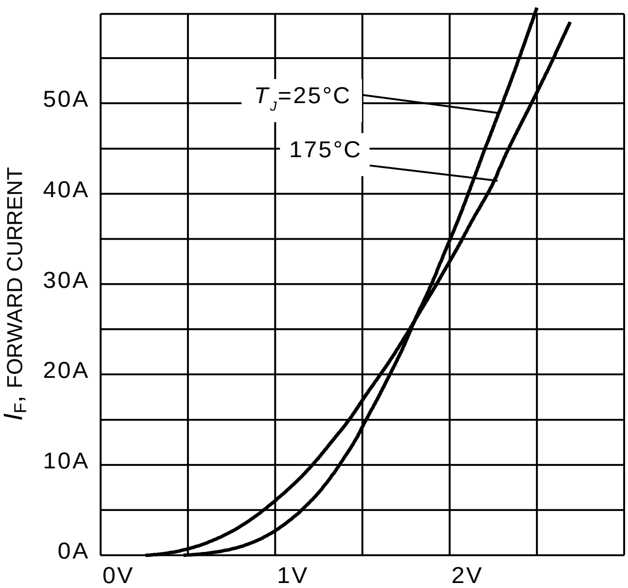


Figure 27. Typical diode forward current as a function of forward voltage

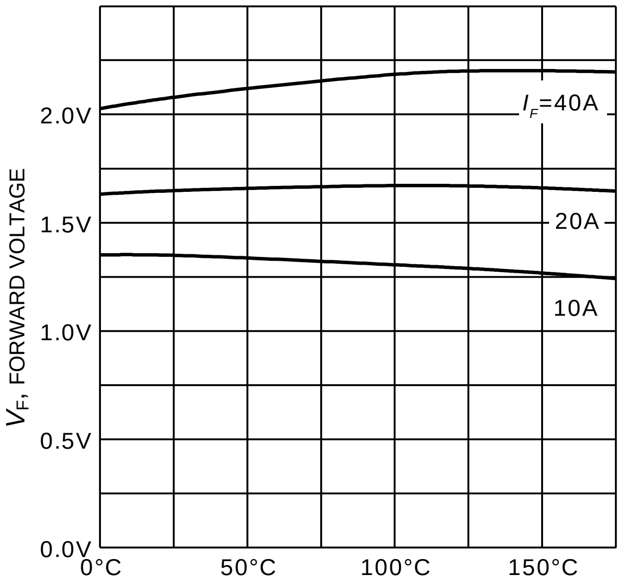
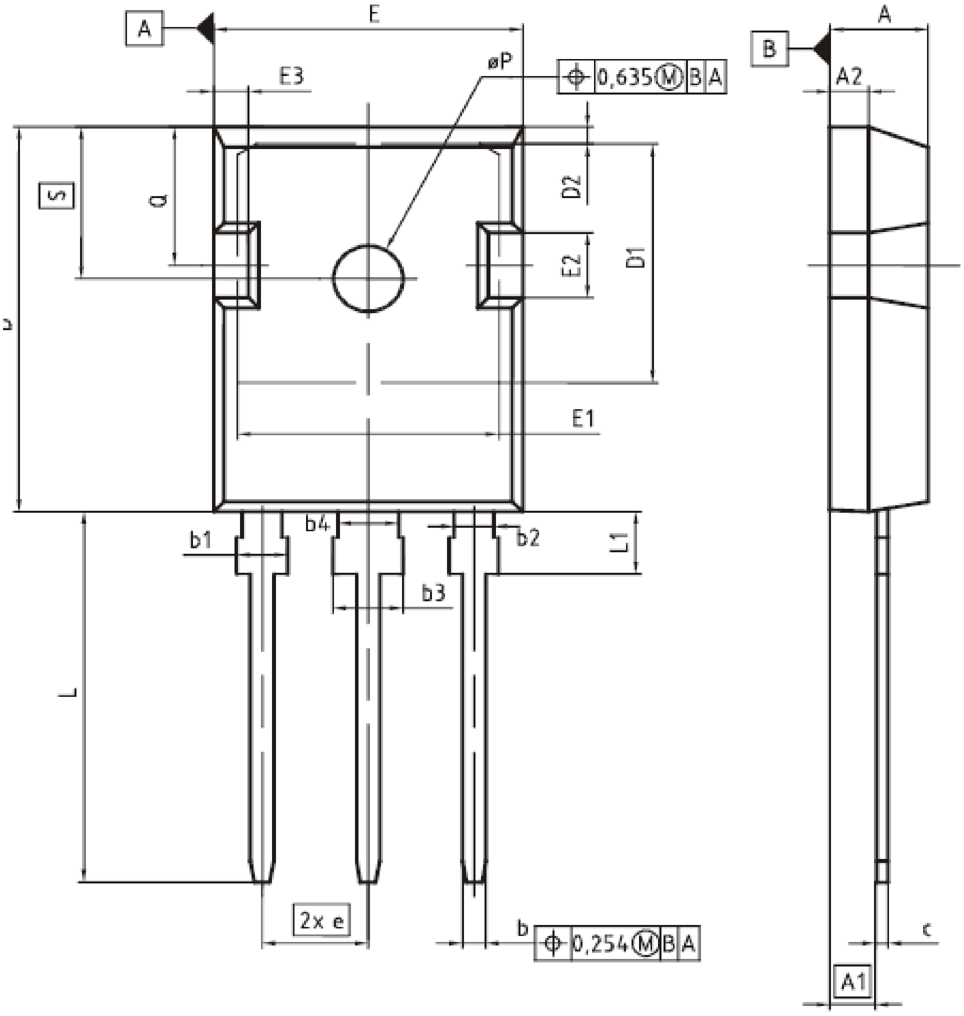


Figure 28. Typical diode forward voltage as a function of junction temperature

PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

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SCALE 0 5 7.5mm

EUROPEAN PROJECTION

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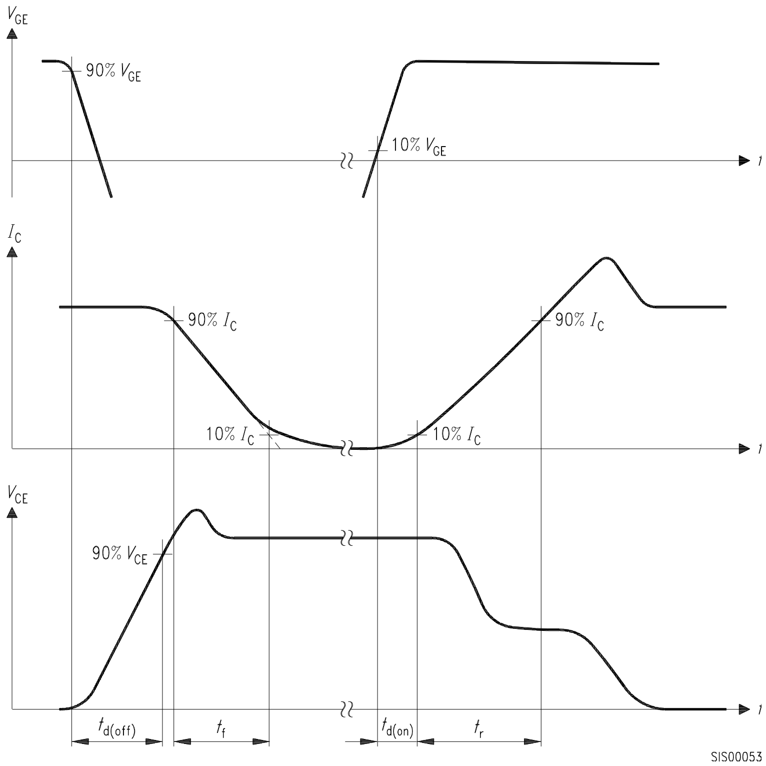

Figure A. Definition of switching times

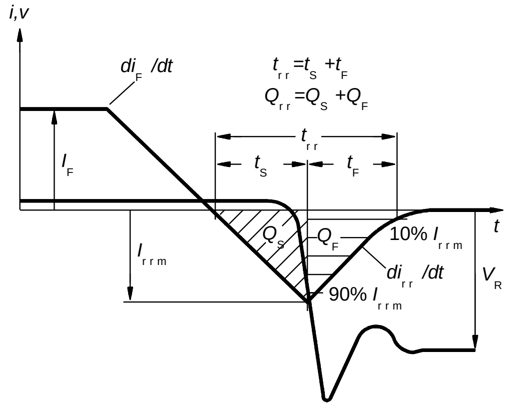

Figure C. Definition of diodes switching characteristics

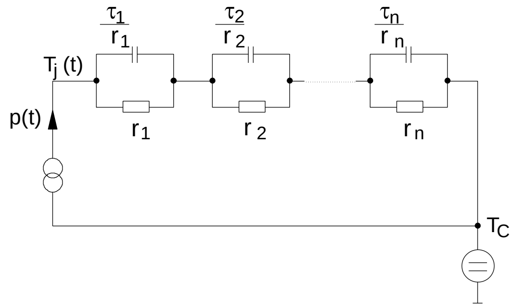

Figure D. Thermal equivalent circuit

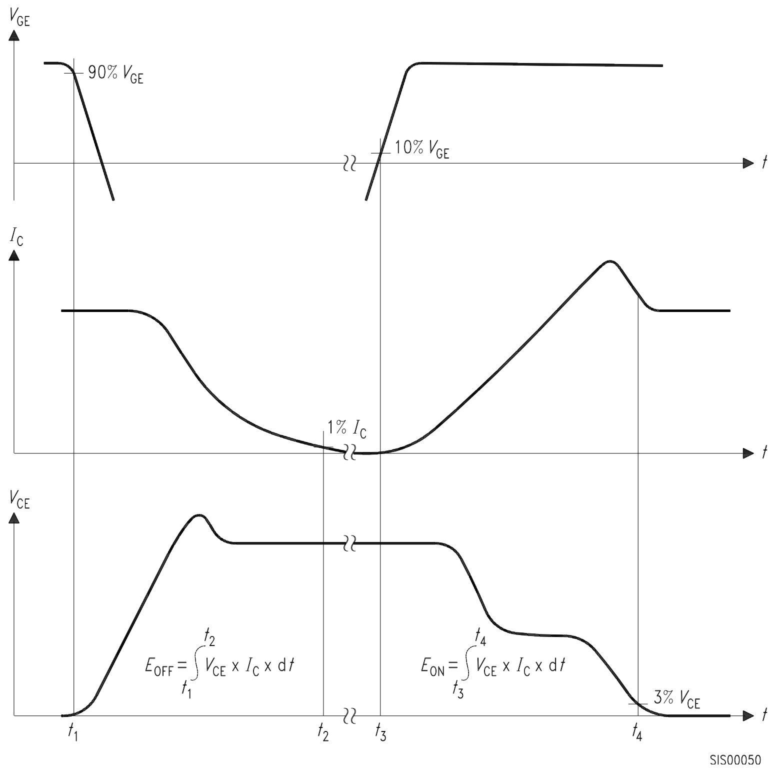

Figure B. Definition of switching losses

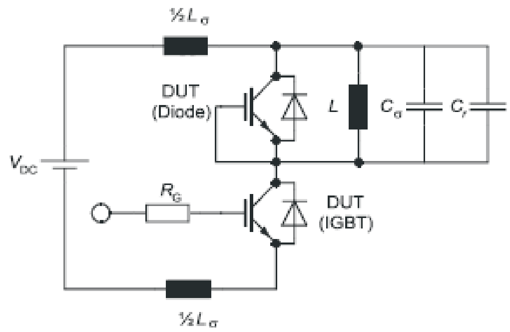

Figure E. Dynamic test circuit
Parasitic inductance L_σ,
Parasitic capacitor C_σ,
Relief capacitor C_r
(only for ZVT switching)

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Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:
moschip.ru
moschip.ru_4
moschip.ru_6
moschip.ru_9